

### EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee. Authorization for this examiner's amendment was given in a telephone interview with Applicant's Representative Andrew J. Taska (Reg. No.: 54,666) on December 3, 2009. The application has been amended as follows:

- **Claim 29:**

The verbiage starting on line 25 (claims filed 11/21/09):

"and an impurity doping region disposed between said first and second channel regions such that a portion of said impurity doping region is not directly..."

has been replaced by:

"and wherein one of said impurity doping regions overlapping said second gate electrode is disposed between said first and second channel regions and has a portion not directly..."

- **Claim 35:** the verbiage starting on line 1

"The thin film transistor substrate according to claim 29, wherein the impurity doping region existing between the second gate electrode and the third gate electrode is an LDD region"

has been replaced by:

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“The thin film transistor substrate according to claim 16, wherein said impurity doping region disposed between said first and second channel regions has a doping concentration and conductivity type of said LDD structure”, thereby letting claim 35 depend on claim 16 instead of depending directly on claim 29. The change in dependence is necessary because of the reference to LDD structure not found as such in claim 29.

- **Claim 36:**

The verbiage:

“said impurity doping region” (line 2) has been replaced by:

“said impurity doping region disposed between said first and second channel regions”.

**Specification:**

- Amendment to the Specification as filed under 37 CFR 1.116 on May 26, 2009, herewith is entered.
- The specification is further amended by replacing “102” on line three (3) of paragraph [24] on page 6 of the specification by “102 =102a, b”;
- The Specification filed 6/10/04 was characterized as “substitute specification”, and serves as the specification amended as set forth above. Said Specification filed 6/120/04 appears identical to the specification as originally filed on 2/9/04. However, with a “substitute specification” a statement that the substitute specification contains no new matter is required. See MPEP 37 C.F.R. 1.125(b).

**Drawings:**

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- The following changes to the drawings have been approved by the examiner and agreed upon by applicant: The Drawings of Figures 2(d), 3(c), 5(c) and 11 have been required to be amended, with implementation offered by applicant's representative's office, to distinguish between 102a and 102b (respectively the first and second active regions), by means of appending "a" to those reference characters "102" pointing to the first active layer (i.e., active layer of the low-voltage transistor on the left), and by appending "b" to those reference characters "102" pointing to the second active layer (i.e., active layer of the high-voltage transistor). In order to avoid abandonment of the application, applicant must make these above agreed upon drawing changes.

#### ***REASON FOR ALLOWANCE***

The following is an examiner's statement of reasons for allowance of claims 14, 16 and 29-36: The argument by appellant as set forth in the appeal brief filed 9/8/09 on pages 13-16 in its entirety, particularly in light of the specification, wherein lightly-doped drain regions (LDD regions) are distinguished from the channel region(s) (see specification, page 17, paragraph [57]). In this regard examiner notes that the region marked "P:4E17/cm<sup>3</sup>" in Nakamura (JP 2003-017502 A) as cited is a lightly doped drain (i.e., LDD) region in both applicant's terminology and as understood by those skilled in the art because said region (a) abuts the drain region, (b) is doped with the same conductivity type (n-type, through phosphorous doping (P)) as the drain region itself, and (c) in an amount that is indeed amply sufficient to ensure said region marked "P:4E17/cm<sup>3</sup>" to be permanently in the ON-state, as asserted by appellant.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to JOHANNES P. MONDT whose telephone number is (571)272-1919. The examiner can normally be reached on 8:00 - 5:30. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Jack W. Keith can be reached on 571-272-6878. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/JOHANNES P MONDT/  
Primary Examiner, Art Unit 3663